

GENERAL DESCRIPTION

This Trench MOSFET has better characteristics, such as fast switching time, low on resistance, low gate charge and excellent avalanche characteristics. It is mainly suitable for DC/DC Converter and Battery pack.

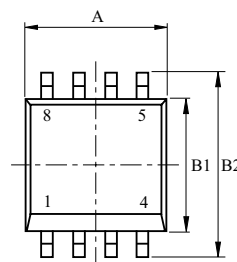
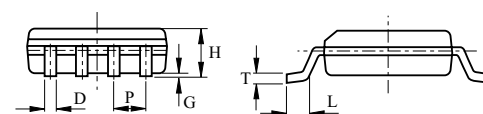
FEATURES

- $V_{DS}=30V$, $I_D=17A$.
- Drain to Source On Resistance.
 $R_{DS(ON)}=5.6m\Omega(\text{Max.}) @ V_{GS}=10V$
 $R_{DS(ON)}=9.7m\Omega(\text{Max.}) @ V_{GS}=4.5V$

MOSFET Maximum Ratings ($T_a=25^\circ\text{C}$ Unless otherwise noted)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Drain to Source Voltage		V_{DS}	30	V
Gate to Source Voltage		V_{GS}	± 20	V
Drain Current	DC@ $T_a=25^\circ\text{C}$ (Note 1)	I_D	17	A
	Pulsed	I_{DP}	68	A
Drain Power Dissipation	@ $T_a=25^\circ\text{C}$ (Note 1)	P_D	2.5	W
Maximum Junction Temperature		T_j	150	$^\circ\text{C}$
Storage Temperature Range		T_{stg}	-55~150	$^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)		R_{thJA}	50	$^\circ\text{C}/\text{W}$

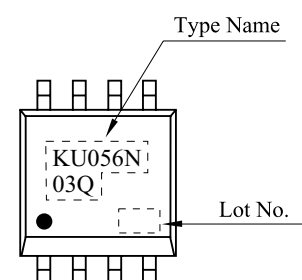
Note1) Surface Mounted on 1"×1" FR4 Board, $t \leq 10\text{sec}$.



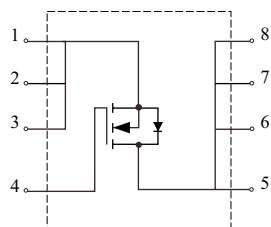
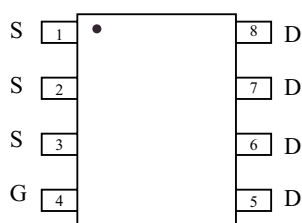
DIM	MILLIMETERS
A	4.85 ± 0.2
B1	3.94 ± 0.2
B2	6.02 ± 0.3
D	0.4 ± 0.1
G	$0.15 + 0.1/-0.05$
H	1.63 ± 0.2
L	0.65 ± 0.2
P	1.27
T	$0.20 + 0.1/-0.05$

FLP-8

Marking



PIN CONNECTION (TOP VIEW)



ELECTRICAL CHARACTERISTICS (Ta=25°C) UNLESS OTHERWISE NOTED

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Static							
Drain to Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250 μA	30	-	-	V
Drain Cut-off Current		I _{DSS}	V _{GS} =0V, V _{DS} =30V	-	-	1	μA
Gate to Source Leakage Current		I _{GSS}	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
Gate to Source Threshold Voltage		V _{th}	V _{DS} =V _{GS} , I _D =250 μA	1.0	-	3.0	V
Drain to Source On Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =17A (Note2)	-	4.7	5.6	mΩ
			V _{GS} =4.5V, I _D =14A (Note2)	-	8.1	9.7	
Forward Transconductance		g _{fs}	V _{DS} =5V, I _D =17A (Note2)	-	68	-	S
Dynamic							
Input Capacitance		C _{iss}	V _{DS} =15V, V _{GS} =0V, f=1MHz (Note2)	-	2772	-	pF
Ouput Capacitance		C _{oss}		-	550	-	
Reverse Transfer Capacitance		C _{rss}		-	398	-	
Gate Resistance		R _g	f=1MHz	-	3.5	-	Ω
Total Gate Charge	V _{GS} =10V	Q _g	V _{DS} =15V, V _{GS} =10V, I _D =17A (Note2)	-	64.5	-	nC
	V _{GS} =4.5V			-	32.2	-	
Gate to Source Charge		Q _{gs}		-	8.0	-	
Gate to Drain Charge		Q _{gd}		-	14.3	-	
Turn-On Delay Time		t _{d(on)}	V _{DS} =15V, V _{GS} =10V I _D =17A, R _G =1.6Ω (Note2)	-	11.0	-	ns
Turn-On Rise Time		t _r		-	15.8	-	
Turn-Off Delay Time		t _{d(off)}		-	58.2	-	
Turn-Off Fall Time		t _f		-	20.0	-	
Source to Drain Diode Ratings							
Source to Drain Forward Voltage		V _{SD}	V _{GS} =0V, I _S =17A (Note2)	-	0.8	1.2	V
Reverse Recovery Time		t _{rr}	I _S =17A, dI/dt=100A/ μs	-	26.1	-	ns
Reverse Recovery Charge		Q _{rr}	I _S =17A, dI/dt=100A/ μs	-	17.3	-	nC
Note2) Pulse Test : Pulse Width≤300μs, Duty Cycle≤2%							

Fig1. $I_D - V_{DS}$

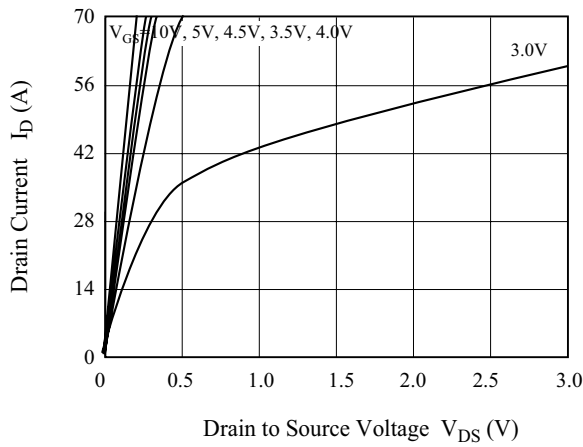


Fig2. $R_{DS(on)} - I_D$

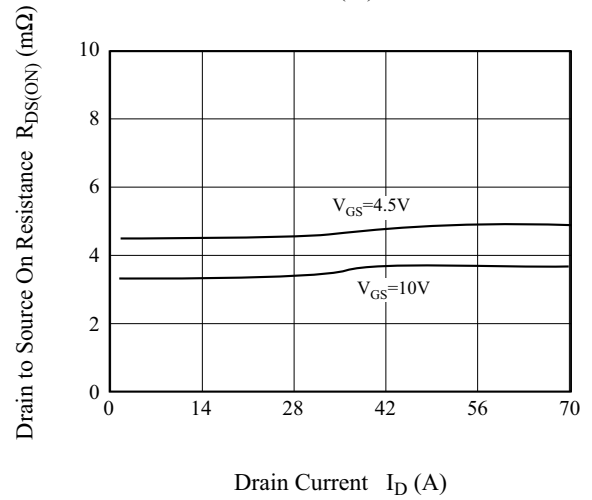


Fig3. $I_D - V_{GS}$

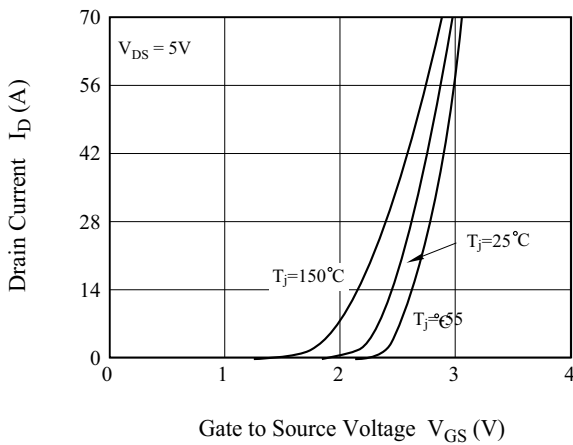


Fig4. $R_{DS(on)} - T_j$

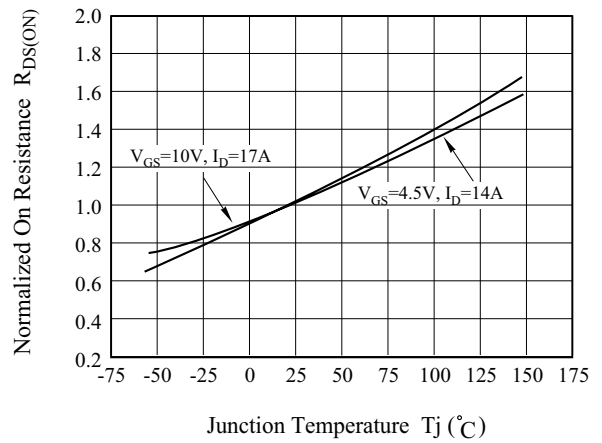


Fig5. $V_{th} - T_j$

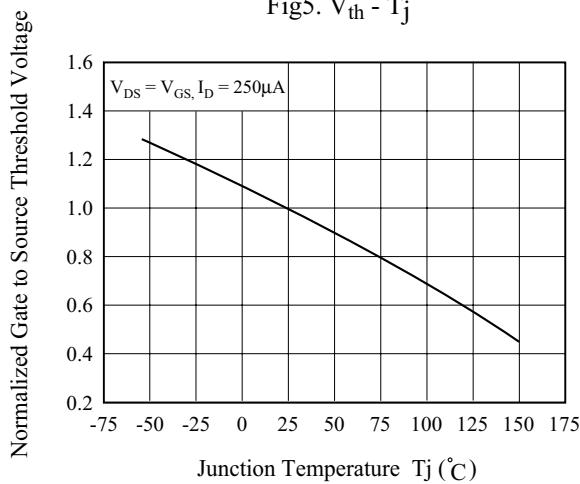


Fig6. $I_S - V_{SD}$

